

Fabio Bernardini

List of Publications by Year in descending order

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105
papers

9,091
citations

109321

35
h-index

39675

94
g-index

107
all docs

107
docs citations

107
times ranked

5892
citing authors

#	ARTICLE	IF	CITATIONS
1	A Synthetic Aperture UHF RFID Localization Method by Phase Unwrapping and Hyperbolic Intersection. IEEE Transactions on Automation Science and Engineering, 2022, 19, 933-945.	5.2	24
2	Thin-Film Aspects of Superconducting Nickelates. Frontiers in Physics, 2022, 10, .	2.1	4
3	Topotactic fluorination of intermetallics as an efficient route towards quantum materials. Nature Communications, 2022, 13, 1462.	12.8	7
4	A UHF-RFID Multi-Antenna Sensor Fusion Enables Item and Robot Localization. IEEE Journal of Radio Frequency Identification, 2022, 6, 456-466.	2.3	14
5	Geometric effects in the infinite-layer nickelates. Physical Review Materials, 2022, 6, .	2.4	13
6	Performance Assessment of a UHF-RFID Robotic Inventory System for Industry 4.0. , 2022, , .		1
7	Robot-Based Indoor Positioning of UHF-RFID Tags: The SAR Method With Multiple Trajectories. IEEE Transactions on Instrumentation and Measurement, 2021, 70, 1-15.	4.7	59
8	Self-Locating RFID Robot for Tag Localization in Retail. , 2021, , .		2
9	Nickelate Superconductors: An Ongoing Dialog between Theory and Experiments. Journal of Experimental and Theoretical Physics, 2021, 132, 618-627.	0.9	41
10	Single-layer T'-type nickelates: Ni is Ni Physical Review Materials, 2021, 5, .	2.4	5
11	Intrinsic thermoelectric figure of merit of bulk compositional SiGe alloys: A first-principles study. Physical Review Materials, 2021, 5, .	2.4	9
12	Engineering the Thermal Conductivity of Doped SiGe by Mass Variance: A First-Principles Proof of Concept. Frontiers in Mechanical Engineering, 2021, 7, .	1.8	2
13	RFID-Based Localization Enables a Smart System for Worker Safety. , 2021, , .		7
14	Past, Present and Future RFID Activities at the University of Pisa. , 2021, , .		0
15	The MONITOR Project: RFID-based Robots enabling real-time inventory and localization in warehouses and retail areas. , 2021, , .		4
16	RFID-Based Tracking for Worker Safety in Industrial Scenario. , 2021, , .		6
17	Special issue on novel superconducting and magnetic materials. Journal of Physics Condensed Matter, 2020, 32, 040401.	1.8	0
18	Infinite-layer fluoro-nickelates as Ni model materials. JPhys Materials, 2020, 3, 035003.	4.2	15

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19	Evidence of nodal superconductivity in LaFeSiH. <i>Physical Review B</i> , 2020, 101, .	3.2	3
20	Particle Swarm Optimization in SAR-Based Method Enabling Real-Time 3D Positioning of UHF-RFID Tags. <i>IEEE Journal of Radio Frequency Identification</i> , 2020, 4, 300-313.	2.3	45
21	many-body correlations in the electronic structure of LaNiO_2 . <i>Physical Review B</i> , 2020, 101, .	3.2	31
22	Stability and electronic properties of $\text{LaNiO}_2/\text{SrTiO}_3$ heterostructures. <i>JPhys Materials</i> , 2020, 3, 03LT01.	4.2	27
23	Magnetic penetration depth and T_c in superconducting nickelates. <i>Physical Review Research</i> , 2020, 2, .	2.4	24
24	Towards a Multi-antenna approach for UHF-RFID tag 3D localization with a Synthetic Aperture Radar Method. , 2019, , .		6
25	Evidence of the isoelectronic character of F doping in $\text{SmFeAsO}_{1-x}\text{F}_x$: a first-principles investigation. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 244001.	1.8	5
26	Particle Swarm Optimization in Multi-Antenna SAR-based Localization for UHF-RFID Tags. , 2019, , .		12
27	Disorder-induced localisation and suppression of superconductivity in $\text{YSr}_2\text{Cu}_3\text{O}_{6+x}$. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 284001.	1.8	1
28	Magnetic competition in Fe-based germanide and silicide superconductors. <i>Europhysics Letters</i> , 2019, 128, 47004.	2.0	3
29	Iron-based superconductivity extended to the novel silicide LaFeSiH. <i>Physical Review B</i> , 2018, 97, .	3.2	22
30	The puzzling structure of Cu_5FeS_4 (bornite) at low temperature. <i>Acta Crystallographica Section B: Structural Science, Crystal Engineering and Materials</i> , 2018, 74, 405-415.	1.1	6
31	Origin of the critical temperature discontinuity in superconducting sulfur under high pressure. <i>Physical Review B</i> , 2017, 95, .	3.2	19
32	Quantum oscillations in the SmFeAsO parent compound and superconducting $\text{SmFeAs}(\text{O},\text{F})$. <i>Physical Review B</i> , 2017, 96, .	3.2	6
33	Unconventional Disorder Effects in Correlated Superconductors. <i>Physical Review Letters</i> , 2016, 117, 257002.	7.8	30
34	The phase diagrams of iron-based superconductors: Theory and experiments. <i>Comptes Rendus Physique</i> , 2016, 17, 5-35.	0.9	44
35	Understanding the $\frac{1}{4}$ SR spectra of MnSi without magnetic polarons. <i>Physical Review B</i> , 2014, 89, .	3.2	40
36	A magnetic glassy phase in $\text{Fe}_{1+y}\text{SexTe}$ single crystals. <i>Journal of Physics Condensed Matter</i> , 2013, 25, 156004.	1.8	9

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37	Role of Dirac cones in magnetotransport properties of REFeAsO (RE = rare earth) oxypnictides. European Physical Journal B, 2013, 86, 1.	1.5	16
38	Theoretical investigation of FeTe magnetic ordering under hydrostatic pressure. Physical Review B, 2013, 87, .	3.2	17
39	<i>Ab initio</i> strategy for muon site assignment in wide band gap fluorides. Physical Review B, 2013, 87, . Common effect of chemical and external pressures on the magnetic properties of	3.2	54

40

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55	Effect of Magnetic Impurities in a Two-Band Superconductor: A Point-Contact Study of Mn-Substituted MgB ₂ Single Crystals. <i>Physical Review Letters</i> , 2006, 97, 037001.	7.8	35
56	Anomalous effect of Li-Al codoping in MgB ₂ : A simple explanation. <i>Physical Review B</i> , 2006, 74, .	3.2	21
57	Interaction of doping impurities with the 30° partial dislocations in SiC: An ab initio investigation. <i>Physical Review B</i> , 2005, 72, .	3.2	16
58	Energetic stability and magnetic properties of Mn dimers in silicon. <i>Applied Physics Letters</i> , 2004, 84, 2289-2291.	3.3	52
59	Energetics of native point defects in cubic silicon carbide. <i>European Physical Journal B</i> , 2004, 38, 437-444.	1.5	22
60	Defect energetics of ¹² SiC using a new tight-binding molecular dynamics model. <i>Journal of Nuclear Materials</i> , 2004, 329-333, 1219-1222.	2.7	18
61	Electronics and sensors based on pyroelectric AlGa _N /Ga _N heterostructures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 1878-1907.	0.8	65
62	Bi incorporation in Ga _N and Al _x Ga _{1-x} N alloys. <i>Physical Review B</i> , 2003, 68, .	3.2	5
63	CORRELATION BETWEEN LOCAL OXYGEN DISORDER AND ELECTRONIC PROPERTIES IN SUPERCONDUCTING RESR ₂ CU ₃ O _{6+X} (RE = Y, YB). <i>International Journal of Modern Physics B</i> , 2003, 17, 873-878.	2.0	3
64	Electronic, dynamical and superconducting properties of MgB ₂ : doping, surface and pressure effects. <i>Superconductor Science and Technology</i> , 2003, 16, 137-142.	3.5	2
65	Stability of Ge-related point defects and complexes in Ge-doped SiO ₂ . <i>Physical Review B</i> , 2002, 66, .	3.2	16
66	Electronic and dynamical properties of the MgB ₂ surface: Implications for the superconducting properties. <i>Physical Review B</i> , 2002, 66, .	3.2	10
67	Self-interstitial trapping by carbon complexes in crystalline silicon. <i>Physical Review B</i> , 2002, 66, .	3.2	45
68	ELECTRONIC AND DYNAMICAL PROPERTIES OF MgB ₂ AND RELATED COMPOUNDS. <i>International Journal of Modern Physics B</i> , 2002, 16, 1563-1569.	2.0	4
69	Evidence for nonlinear macroscopic polarization in III-V nitride alloy heterostructures. <i>Applied Physics Letters</i> , 2002, 80, 1204-1206.	3.3	746
70	First-principles calculation of the piezoelectric tensor d_{33} of III-V nitrides. <i>Applied Physics Letters</i> , 2002, 80, 4145-4147.	3.3	125
71	Pyroelectric properties of Al(In)Ga _N /Ga _N hetero- and quantum well structures. <i>Journal of Physics Condensed Matter</i> , 2002, 14, 3399-3434.	1.8	864
72	Nonlinear Behavior of Spontaneous and Piezoelectric Polarization in III-V Nitride Alloys. <i>Physica Status Solidi A</i> , 2002, 190, 65-73.	1.7	44

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73	Nonlinear macroscopic polarization in III-V nitride alloys. <i>Physical Review B</i> , 2001, 64, .	3.2	272
74	Electronic and structural properties of superconducting MgB ₂ , CaSi ₂ , and related compounds. <i>Physical Review B</i> , 2001, 64, .	3.2	135
75	MgB ₂ and BeB ₂ : A comparative study of their electronic and superconducting properties. <i>Physical Review B</i> , 2001, 65, .	3.2	18
76	Accurate calculation of polarization-related quantities in semiconductors. <i>Physical Review B</i> , 2001, 63, .	3.2	168
77	Proof of the Thermodynamical Stability of the E ² Center in SiO ₂ . <i>Physical Review Letters</i> , 2001, 86, 3064-3067.	7.8	46
78	First-principles prediction of structure, energetics, formation enthalpy, elastic constants, polarization, and piezoelectric constants of AlN, GaN, and InN: Comparison of local and gradient-corrected density-functional theory. <i>Physical Review B</i> , 2001, 64, .	3.2	421
79	Polarization fields in nitride nanostructures: 10 points to think about. <i>Applied Surface Science</i> , 2000, 166, 23-29.	6.1	71
80	Doping screening of polarization fields in nitride heterostructures. <i>Applied Physics Letters</i> , 2000, 76, 3950-3952.	3.3	56
81	Incorporation, diffusion, and electrical activity of Li in GaN. <i>Physical Review B</i> , 2000, 61, 12598-12601.	3.2	8
82	Band offsets and stability of BeTe/ZnSe (100) heterojunctions. <i>Physical Review B</i> , 2000, 62, R16302-R16305.	3.2	14
83	Theoretical evidence for the semi-insulating character of AlN. <i>Journal of Applied Physics</i> , 1999, 85, 2001-2003.	2.5	52
84	Free-carrier screening of polarization fields in wurtzite GaN/InGaN laser structures. <i>Applied Physics Letters</i> , 1999, 74, 2002-2004.	3.3	268
85	Spontaneous versus Piezoelectric Polarization in III-V Nitrides: Conceptual Aspects and Practical Consequences. <i>Physica Status Solidi (B): Basic Research</i> , 1999, 216, 391-398.	1.5	271
86	Effects of macroscopic polarization in III-V nitride multiple quantum wells. <i>Physical Review B</i> , 1999, 60, 8849-8858.	3.2	488
87	Macroscopic polarization and band offsets at nitride heterojunctions. <i>Physical Review B</i> , 1998, 57, R9427-R9430.	3.2	371
88	Electronic dielectric constants of insulators calculated by the polarization method. <i>Physical Review B</i> , 1998, 58, 15292-15295.	3.2	84
89	Valence-band offsets at the Al _x Ga _{0.5-2x} In _{0.5P} -ZnSe(001) lattice-matched interface. <i>Physical Review B</i> , 1997, 55, 1718-1723.	3.2	2
90	Band offsets at the GaInP/GaAs heterojunction. <i>Journal of Applied Physics</i> , 1997, 82, 3374-3380.	2.5	26

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91	Theoretical evidence for efficient p-type doping of GaN using beryllium. Applied Physics Letters, 1997, 70, 2990-2992.	3.3	102
92	Polarization-Based Calculation of the Dielectric Tensor of Polar Crystals. Physical Review Letters, 1997, 79, 3958-3961.	7.8	236
93	Spontaneous polarization and piezoelectric constants of III-V nitrides. Physical Review B, 1997, 56, R10024-R10027.	3.2	2,662
94	The luminescence transition in porous silicon: the nature of the electronic states. Thin Solid Films, 1996, 276, 261-264.	1.8	2
95	Electron states and luminescence transition in porous silicon. Physical Review B, 1996, 53, 4557-4564.	3.2	41
96	Si/CaF ₂ Superlattices. A Direct Gap Structure Due to Interface State Coupling. Physica Status Solidi (B): Basic Research, 1995, 190, 117-122.	1.5	9
97	Light Emission at Room Temperature from Si/CaF ₂ Multilayers. Europhysics Letters, 1995, 31, 25-30.	2.0	43
98	Electronic structure of thin Si layers in CaF ₂ : Hybridization versus confinement. Solid-State Electronics, 1994, 37, 1145-1147.	1.4	0
99	Gap opening in ultrathin Si layers: Role of confined and interface states. Physical Review Letters, 1994, 72, 1044-1047.	7.8	31
100	First-principles investigation of the electronic structure of Si-based layered structures. Surface Science, 1994, 307-309, 984-988.	1.9	2
101	Electronic Properties of Low Dimensional Silicon Structures. , 1993, , 219-228.		2
102	Hydrogen covered Si(111) surfaces. Surface Science, 1992, 269-270, 879-885.	1.9	35
103	Fermi-level pinning and interface states at Pb ²⁺ -Si(111) interface. Solid State Communications, 1992, 82, 863-866.	1.9	2
104	Hydrogen on semiconductor surfaces. Physica B: Condensed Matter, 1991, 170, 429-435.	2.7	16
105	Chemisorption of H on GaAs(110): a First-Principles Calculation. Europhysics Letters, 1990, 13, 653-658.	2.0	26